



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(on)} | I _D T _A = +25℃ |
|----------------------|-------------------------------|---|
| 60V | 66mΩ @ V _{GS} = 10V | 5.0A |
| 60 v | 97mΩ @ V _{GS} = 4.5V | 4.1A |

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features and Benefits

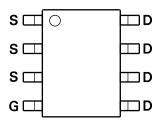
- Low on-resistance
- Fast switching speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

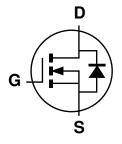
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ²³
- Weight: 0.074 grams (Approximate)







Top View



Equivalent Circuit

Ordering Information (Notes 4 & 5)

| Part Number | Compliance | Case | Packaging |
|---------------|--------------|------|-------------------|
| DMN6066SSS-13 | B Commercial | SO-8 | 2,500/Tape & Reel |
| DMN6066SSSQ-1 | 3 Automotive | SO-8 | 2,500/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

N6066SS • YY WW

SO-8

Oll = Manufacturer's Marking N6066SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01 - 53)



Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit V |
|-----------------------------|-----------------------|----------------------------------|-----------------|-------|-----------|
| Drain-Source Voltage | | V _{DSS} | 60 | | |
| Gate-Source Voltage (Note 6 | | (Note 6) | V _{GS} | ±20 | V |
| Single Pulsed Avalanche En | ergy | (Note 11) | E _{AS} | 37.5 | mJ |
| Single Pulsed Avalanche Cu | ırrent | (Note 11) | I _{AS} | 5.0 | Α |
| Continuous Drain Current | | (Note 8) | | 5.0 | |
| | $V_{GS} = 10V$ | T _A = +70 °C (Note 8) | I _D | 4.0 | Α |
| | | (Note 7) | | 3.7 | |
| Pulsed Drain Current | V _{GS} = 10V | (Note 9) | I _{DM} | 23 | Α |
| Continuous Source Current | (Body diode) | (Note 8) | I _S | 4.0 | Α |
| Pulsed Source Current (Bod | y diode) | (Note 9) | I _{SM} | 23 | Α |

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

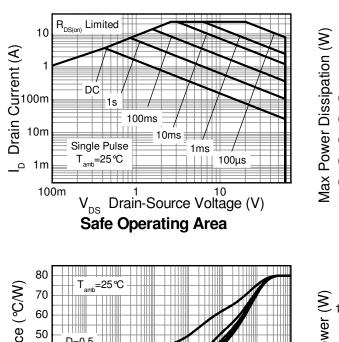
| Characteristic | | Symbol | Value | Unit | |
|---|-----------|-----------------------------------|--------------|-----------|--|
| Power Dissipation | (Note 7) | 9 | 1.56 12.5 | W mW/℃ | |
| Linear Derating Factor | (Note 8) | PD | 2.81 22.5 | | |
| Thermal Resistance, Junction to Ambient | (Note 7) | R _e JA | 80.0 | | |
| Thermal Hesistance, Junction to Ambient | (Note 8) | П _Ө ЈА | 44.5 | °C/W | |
| Thermal Resistance, Junction to Lead | (Note 10) | $R_{	heta JL}$ | 37.0 | | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to 150 | ℃ | |

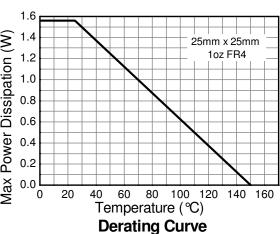
Notes:

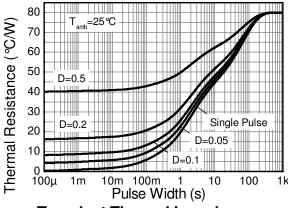
- 6. AEC-Q101 V_{GS} maximum is ±16V.
 7. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 8. Same as note (7), except the device is measured at t ≤ 10 sec.
 9. Same as note (7), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
- 10. Thermal resistance from junction to solder-point (at the end of the drain lead).
- 11. UIS in production with L = 3.0mH, I_{AS} = 5.0A, R_G = 25 Ω , V_{DD} =50V, starting T_J = +25 $^{\circ}$ C.



Thermal Characteristics







Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

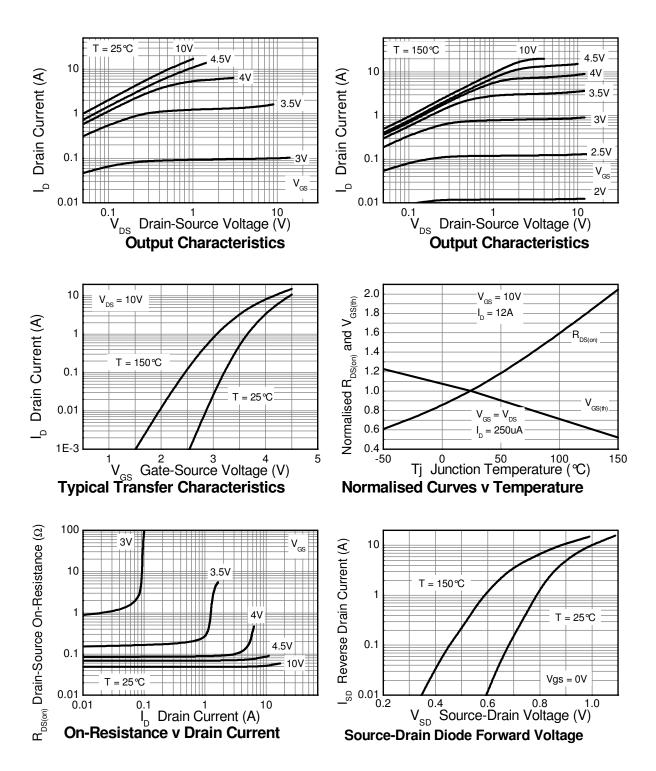
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|---|----------------------|-----|-------|-------|------|--|--|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | _ | _ | V | $I_D = 250 \mu A, V_{GS} = 0 V$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 0.5 | μΑ | $V_{DS} = 60V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 1.0 | _ | 3.0 | V | $I_D=250\mu A,\ V_{DS}=V_{GS}$ | |
| Statia Drain Saurea On Desigtance (Note 12) | Б | | 0.048 | 0.066 | Ω | $V_{GS} = 10V, I_D = 4.5A$ | |
| Static Drain-Source On-Resistance (Note 12) | R _{DS} (ON) | _ | 0.068 | 0.097 | 12 | $V_{GS} = 4.5V, I_D = 3.5A$ | |
| Forward Transconductance (Notes 12 & 13) | 9fs | _ | 19.2 | _ | S | $V_{DS} = 15V, I_D = 6A$ | |
| Diode Forward Voltage (Note 12) | V _{SD} | _ | 0.89 | 1.15 | V | $I_S = 4.5A, V_{GS} = 0V$ | |
| Reverse Recovery Time (Note 13) | t _{rr} | | 23 | _ | ns | -I _S = 2.4A, di/dt = 100A/μs | |
| Reverse Recovery Charge (Note 13) | Qrr | _ | 19.7 | _ | nC | | |
| DYNAMIC CHARACTERISTICS (Note 13) | | | | | | | |
| Input Capacitance | C _{iss} | | 502 | _ | pF | | |
| Output Capacitance | Coss | | 45.7 | _ | pF | $V_{DS} = 30V, V_{GS} = 0V$ -f = 1MHz | |
| Reverse Transfer Capacitance | C _{rss} | _ | 27.1 | _ | рF | 1 – 11011 12 | |
| Total Gate Charge (Note 14) | Qg | _ | 5.4 | _ | nC | V _{GS} = 4.5V | |
| Total Gate Charge (Note 14) | Qg | _ | 10.3 | _ | nC | V _{DS} = 30V | |
| Gate-Source Charge (Note 14) | Q _{gs} | _ | 1.7 | _ | nC | $V_{GS} = 10V$ $I_D = 4.5A$ | |
| Gate-Drain Charge (Note 14) | Q _{gd} | _ | 3.2 | _ | nC | 1 | |
| Turn-On Delay Time (Note 14) | t _{D(on)} | _ | 2.7 | _ | ns | $V_{DD}=30V,V_{GS}=10V$ $I_{D}=1A,R_{G}\cong6.0\Omega$ | |
| Turn-On Rise Time (Note 14) | tr | _ | 2.4 | | ns | | |
| Turn-Off Delay Time (Note 14) | t _{D(off)} | _ | 14.7 | | ns | | |
| Turn-Off Fall Time (Note 14) | t _f | | 5.4 | _ | ns | | |

Notes:

^{12.} Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.

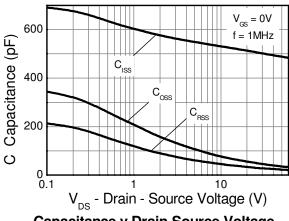


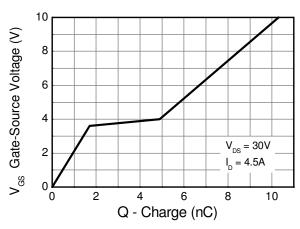
Typical Characteristics





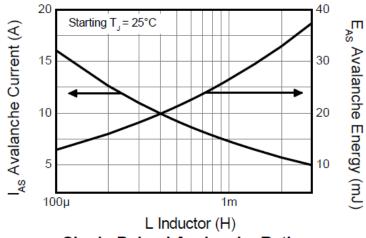
Typical Characteristics (continued)





Capacitance v Drain-Source Voltage

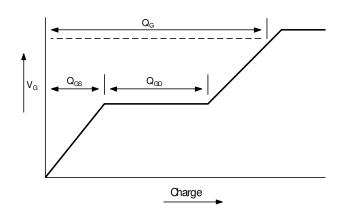
Gate-Source Voltage v Gate Charge

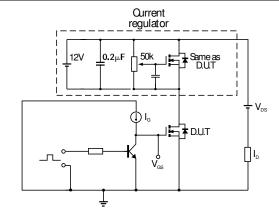


Single-Pulsed Avalanche Rating



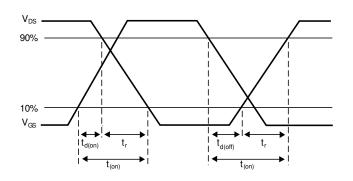
Test Circuits

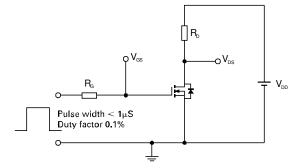




Basic gate charge waveform

Gate charge test circuit





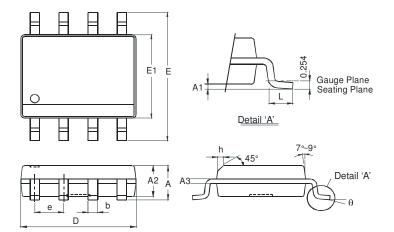
Switching time waveforms

Switching time test circuit



Package Outline Dimensions

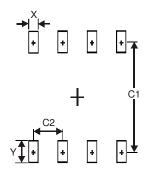
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| SO-8 | | | | |
|----------------------|----------|------|--|--|
| Dim | Min | Max | | |
| Α | - | 1.75 | | |
| A1 | 0.10 | 0.20 | | |
| A2 | 1.30 | 1.50 | | |
| А3 | 0.15 | 0.25 | | |
| b | 0.3 | 0.5 | | |
| D | 4.85 | 4.95 | | |
| Е | 5.90 | 6.10 | | |
| E1 | 3.85 | 3.95 | | |
| е | 1.27 Typ | | | |
| h | - | 0.35 | | |
| L | 0.62 | 0.82 | | |
| Θ | 0° 8° | | | |
| All Dimensions in mm | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| X | 0.60 |
| Υ | 1.55 |
| C1 | 5.4 |
| C2 | 1.27 |



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